SEMICONDUCTOR CONSTRUCTION WITH ISOLATION REGIONS FOR DRAM CELL AND PRODUCTION METHOD

ABSTRACT

The invention includes semiconductor constructions containing vertically-extending pillars (80, 82) and methods for forming such constructions. The vertically-extending pillars can be incorporated into transistor devices (80, 95) and can contain vertically-extending channel regions of the transistor devices. The transistor devices can be incorporated into integrated circuitry, and in some aspects are incorporated into memory constructions, such as, for example, dynamic random access memory (DRAM) constructions.

FIGURE 16